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(54) SiO_x POROUS COMPACT

(57)Abstract:

PROBLEM TO BE SOLVED: To provide an SiO_x porous compact low in vapor deposition temperature, also high in an evaporation rate and good in vapor deposition efficiency when used as the raw material for vapor deposition.

SOLUTION: This porous compact contains SiO_x ($0.8 < x \leq 1.5$) and also has a specific gravity of 0.4 to 1.2 and a specific area ratio of ≥ 10 m²/g. Further, the raw material for vapor deposition is composed of the SiO_x porous compact.

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